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Table of Contents

Trends in Microwave/Millimeter-Wave Front-End Technology	1
<i>Gailon E. Brehm</i>	
Solutions for Input Impedance Matching of Nanodevices: Application to Y-Branch Junction HF to DC Rectifier	5
<i>Lukasz Bednarz, Rashmi, Ghania Farhi, Benoit Hackens, Vincent Bayot, Isabelle Huynen</i>	
Noise and Dynamic Cryogenic performance of Metamorphic Transistors from 20 to 42 GHz.....	9
<i>Sébastien Delcourt, Gilles Dambrine, Nour Eddine Bourzgui, Sylvie Lepilliet, Christophe Laporte, Derek Smith, Jean-Philippe Frayssé</i>	
Electromagnetic-Thermal Analysis for Inductances and Eddy Current Losses of On-chip Spiral Inductors on Lossy Silicon Substrate	13
<i>Kai Kang, Le-Wei Li, Said Zouhdi, Jinglin Shi, Wen-Yan Yin</i>	
The Role and Mechanism of Fe-ion Bombardment in creating highly resistive InGaAs layers	17
<i>S.C. Subramaniam, A.A. Rezazadeh</i>	
Ar Implantation, a Passivation Technique for High-Resistivity Silicon Within the MCM-D Technology	21
<i>G. Posada, G. Carchon, P. Soussan, G. Poesen, Bart Nauwelaers, W. De Raedt</i>	
InP-Based InAlAs/InGaAs Double-Gate Transistors Beyond Conventional HEMT's Limitations	25
<i>N. Wichmann, S. Bollaert, B.G. Vasallo, X. Wallart, Gilles Dambrine, A. Cappy</i>	
Indium Antimonide Based Quantum Well FETs for Ultra-High Frequency, Low Power Dissipation Circuits	29
<i>T. Ashley, L. Buckle, M.T. Emeny, M. Fearn, D.G. Hayes, K.P. Hilton, R. Jefferies, T. Martin, T.J. Phillips, J. Powell, A.W.H. Tang, D.J. Wallis, P.J. Wilding</i>	
Millimeter-Wave Front-End Components in Metamorphic HEMT Technology	31
<i>M. Schlechtweg, I. Kallfass, A. Tessmann, C. Schworer, A. Leuther</i>	
Antenna-Coupled Microbolometers for Passive THz Direct Detection Imaging Arrays	35
<i>P. Helisto, A. Luukanen, L. Gronberg, J.S. Penttila, H. Seppa, H. Sipola, Charles R. Dietlein, E.N. Grossman</i>	
High Efficiency HBV Multipliers	39
<i>Jan Stake, Tomas Bryllert, T. Arezoo Emadi, Mahdad Sadeghi, Josip Vukusic</i>	
Detailed Analysis of DC-RF Dispersion in AlGaIn/GaN HFETs Using Waveform Measurements.....	43
<i>Chris Roff, Peter McGovern, Johannes Benedikt, Paul J. Tasker, R.S. Balmer, D.J. Wallis, K.P. Hilton, J.O. Maclean, D.G. Hayes, M.J. Uren, T. Martin</i>	
Operation of RF Power MOSFETs Under Proton Radiation.....	46
<i>Ningyue Jiang, Zhenqiang Ma, Larry B. Li</i>	
Fabrication, Characterization and Numerical Simulation of High Breakdown Voltage pHEMTs.....	50
<i>A. Chini, S. Lavanga, M. Peroni, C. Lanzieri, A. Cetronio, V. Teppati, V. Camarchia, G. Ghione, G. Verzellesi</i>	
Temperature Analysis of AlGaIn/GaN High-Electron-Mobility Transistors Using Micro-Raman Scattering Spectroscopy and Transient Interferometric Mapping.....	54
<i>E. Pichonat, J. Kuzmik, S. Bychikhin, D. Pogany, M.A. Poisson, B. Grimberty, C. Gaquiere</i>	
Enhanced Design and Performance of Power FETs Based on Electromagnetic Modelling.....	58
<i>David Denis, Ian C. Hunter, Christopher M. Snowden</i>	
Very High Performance GaN HEMT Devices by Optimized Buffer and Field Plate Technology	61
<i>P. Romanini, M. Peroni, C. Lanzieri, A. Cetronio, M. Calori, A. Passaseo, B. Poti, A. Chini, L. Mariucci, A. Di Gaspare, V. Teppati, V. Camarchia</i>	
Control of Short-Channel Effects in GaN/AlGaIn HFETs	65
<i>M.J. Uren, D.G. Hayes, R.S. Balmer, D.J. Wallis, K.P. Hilton, J.O. Maclean, T. Martin, Chris Roff, Peter McGovern, Johannes Benedikt, Paul J. Tasker</i>	

Table of Contents

Enhanced Schottky Gate and Pulsed IV Characteristics of AlGaNGaN HEMT on Si with Gate-Annealing and SiNprotect LY1.underscore X Passivation	69
<i>Jin-Cherl Her, Sung-Won Kim, Kyung-Chul Jang, Gyung-Seon Seol, Min-Koo Han, Jae-Eung Oh, Kwang-Seok Seo</i>	
A 100W Class-E GaN HEMT with 75% Drain Efficiency at 2GHz.....	72
<i>Norihiko Ui, Seigo Sano</i>	
Design and Analysis of a 34 dBm Ka-Band GaN High Power Amplifier MMIC.....	75
<i>M. van Heijningen, F.E. van Vliet, R. Quay, F. van Raay, M. Seelmann-Eggebert</i>	
A Method to Design Distributed Harmonic Matching Networks	79
<i>Paolo Colantonio, Franco Giannini, Lucio Scucchia</i>	
Generic Robust LVC MOS-Compatible Control Logic for GaAs HEMT Switches	83
<i>M. van Wanum, G. van der Bent, M. Rodenburg, A.P. de Hek</i>	
InP DHBT Based MMICs for [DC-20 GHz] Signal Sampling.....	87
<i>Hassan El Aabbaoui, Benoit Gorisse, Aziz Benlarbi-Delai, Nathalie Rolland, Virginie Allouche, Nicolas Fel, Bernard Riondet, Pascal Leclerc, Paul-Alain Rolland</i>	
CAD Techniques for 183GHz Fixed Tuned Sub-Harmonic Mixer Using Foundry Diodes	91
<i>Steve Marsh, Byron Alderman, Dave Matheson, Peter de Maagt</i>	
Behavioral Modeling of Microwave Amplifiers Including Large-Signal and Noise Interaction	95
<i>Cedric Chambon, Laurent Escotte, Eric Gonneau</i>	
Nonlinear and Memory Characterization of GaAs FET Devices and FET-Based Power Amplifier Circuits.....	99
<i>Jon Santiago, Joaquin Portilla, Tomas Fernandez</i>	
77GHz Low Noise Sub Block MMICs with 120 nm Inprotect LY1.underscore 0.4AlAs/Inprotect LY1.underscore 0.35GaAs Metamorphic HEMTs	103
<i>Sung-Won Kim, Dong-Hwan Kim, Jin-Cherl Her, Kyung-Chul Jang, Woo-Yeol Choi, Young-Woo Kwon, Kwang-Seok Seo</i>	
Configuration Dependence of SiGe HBT Linearity Characteristics	107
<i>Guoxuan Qin, Ningyue Jiang, Guogong Wang, Zhenqiang Ma</i>	
Bias and Temperature Dependant Third Order Nonlinearity of GaAs DHBTs and its use in Extracting Thermal Resistance	111
<i>A. Khan, A.A. Rezazadeh</i>	
Low-Frequency Noise Measurements of Bipolar Devices Under High DC Current Density: Whether Transimpedance or Voltage Amplifiers.....	114
<i>A.A. Lisboa de Souza, J.-C. Nallatamby, M. Prigent</i>	
4--8 GHz Low Noise Amplifiers Using Metamorphic HEMT Technology	118
<i>Matthew Kelly, I. Angelov, J. Piotr Starski, Niklas Wadefalk, Herbert Zirath</i>	
An Integrated Low Noise Amplifier and Image-rejection Mixer in a Surface Mount Package for Low Cost 10--22GHz Applications	122
<i>Khanhtran Phan, Kohei Fujii, Henrik Morkner, Alan Rixon</i>	
Ultra Low Noise Amplifier in SiGe:C Technology for 802.11a, b and g WLAN Applications	126
<i>Hans-Peter Forstner, Alfons Dehe, Bernd Eisener, Klaus Ettinger, Udo Gerlach, Andrea Jentzsch, Wolfgang Klein, Christian Lehrer</i>	
A Low Noise and Low Power, SiGe-BiCMOS LNA for IEEE 802.11a Applications.....	129
<i>Mehmet Kaynak, Ibrahim Tekin, Ayhan Bozkurt, Yasar Gurbuz</i>	
Design of a Fully Integrated Switchable Transistor CMOS LNA for 2.1 / 2.4 GHz Application	133
<i>Wang-Chi Cheng, Jian-Guo Ma, Kiat-Seng Yeo, Manh-Anh Do</i>	

Table of Contents

220 GHz Low-Noise Amplifier Modules for Radiometric Imaging Applications	137
<i>A. Tessmann, A. Leuther, M. Kuri, H. Massler, M. Riessle, H. Essen, S. Stanko, R. Sommer, M. Zink, R. Stibal, W. Reinert, M. Schlechtweg</i>	
A GaAs HBT Low Power 24 GHz Downconverter with On-Chip Local-Oscillator	141
<i>C. Meliani, Meik Huber, Georg Boeck, Wolfgang Heinrich</i>	
Design of Subharmonically Pumped Schottky Mixers for Submillimetre-Wave Applications.....	145
<i>Jose V. Siles, Jesus Grajal, Viktor Krozer</i>	
High Performance PIN Diode in 0.18-(μm) SiGe BiCMOS Process for Broadband Monolithic Control Circuits	149
<i>Pinping Sun, Parag Upadhyaya, Le Wang, Dong-Ho Jeong, Deukhyoun Heo</i>	
First InP/GaAsSb/InP DHBT Ka-Band MMIC Oscillator	153
<i>Xin Zhu, Jing Wang, Dimitris Pavlidis</i>	
Capabilities of a 10 GHz MEMS Based VCO	157
<i>A. Coustou, David Dubuc, Katia Grenier, E. Fourn, O. Llopis, Robert Plana</i>	
4-GHz Fully Monolithic SiGe HBT QVCO Using Superharmonic Coupling Topology	161
<i>S.C. Tseng, C.C. Meng, Y.W. Chang, G.W. Huang</i>	
A Sub-1 V 1.6 GHz CMOS VCO with 29% Tuning Range	165
<i>Wang-Chi Cheng, Cheong-Fat Chan, Kong-Pang Pun, Chiu-Sing Choy</i>	
A 1.3V Low Phase Noise 2-GHz CMOS Quadrature LC VCO	169
<i>Parag Upadhyaya, Deukhyoun Heo, Yi-Jan Emery Chen</i>	
A C-Band Oscillator MMIC with High Output Power, Low Harmonics, and Low Phase Noise Using Passive Buffer	173
<i>Sanghoon Sim, Songcheol Hong</i>	
A Miniature YIG Tuned Oscillator/Frequency Divider Achieves Octave Tuning Bandwidth with Ultra Low Phase Noise in S, C, X and Ku Bands	176
<i>Allen A. Sweet, Ron Parrott</i>	
Fast Settling 9GHz PLL Using 528MHz Reference PLL Clock for MB-OFDM UWB System	179
<i>Young Jae Lee, Seok Bong Hyun, Geum Young Tak, Hyun-Kyu Yu</i>	
Incorporating the Single-Loop Delta-Sigma Modulator in Fractional-N Frequency Synthesizer for Phase-Noise Improvement.....	183
<i>C.J. Li, C.H. Huang, W.H. Ho, T.S. Horng, K.C. Peng</i>	
54 dB Image Rejection Fully Integrated Receiver for Multi-Standard 5-GHz WLANs	187
<i>D. Zito, B. Neri, R. Massini</i>	
High Intercept Point, Broadband, Cost-Effective, and Power-Efficient Passive Reflection FET DBM	190
<i>Ulrich L. Rohde, Ajay K. Poddar</i>	
An Integrated SiGe-BiCMOS Low Noise Transmitter Chip with a Frequency Divider Chain for 77 GHz Applications.....	194
<i>Akbar Ghazinour, Peter Wennekers, Ralf Reuter, Yin Yi, Hao Li, Thomas Bohm, Danny Jahn</i>	
A Fully Differential 60 GHz Receiver Front-End with Integrated PLL in SiGe:C BiCMOS.....	198
<i>Yaoming Sun, Srdjan Glisic, Frank Herzel</i>	
S-Band SiGe Phase and Amplitude Control MMIC	202
<i>F.E. van Vliet, A. de Boer, G.C. Visser</i>	
A Low Cost Packaging Solution for Microwave Applications.....	205
<i>R. Wormald, S. David, G. Panaghiston, R. Jeffries</i>	

Table of Contents

Linear, Noise and Nonlinear HF Models for Advanced CMOS Technology.....	209
<i>F. Danneville, G. Pailloncy, A. Siligaris, D. Gloria, Gilles Dambrine</i>	
Compact RF Modeling of Multiple-Gate MOSFETs.....	213
<i>B. Iniguez, A. Lazaro, O. Moldovan</i>	
CMOS Large Signal and RF Noise Model for CAD	217
<i>I. Angelov, M. Ferndahl, F. Ingvarson, Herbert Zirath, H.O. Vicks</i>	
Advanced Process Modules for (Sub-) 45nm Analog/RF CMOS - Technology Description and Modeling Challenges.....	221
<i>S. Decoutere, V. Subramanian, J. Loo, C. Gustin, B. Parvais, M. Dehan, A. Mercha</i>	
On-Wafer Wideband Characterization of Advanced MOS Technologies.....	225
<i>Jean-Pierre Raskin</i>	
A Compact 500-mW Ku-Band Power Amplifier MMIC in 3x3-mm² Quad Flat (QFN) Packages.....	229
<i>A. Bessemoulin, Y.H. Suh, D. Richardson, S.J. Mahon, J.T. Harvey</i>	
A Very Low Cost Ku-Band 2W Power Amplifier MMIC Using a Plastic-Molded QFN Package	233
<i>Akira Akiyama, Tadayuki Shimura, Tomio Sato, Yuichi Hasegawa</i>	
Multi Function and High Power Amplifier Chipset for X-Band Phased Array Frontends	237
<i>M. van Heijningen, A. de Boer, J.A. Hoogland, M. van Wanum, A.P. de Hek, F.E. van Vliet, H. Brouzes</i>	
Advanced High Power Amplifier Chain for X-Band T/R-Modules Based on GaN MMICs.....	241
<i>P. Schuh, R. Leberer, H. Sledzik, M. Oppermann, B. Adelseck, H. Brugger, R. Quay, M. Mikulla, G. Weimann</i>	
A Compact 8W S/C-Band MMIC Power Amplifier Designed for CW Telemetry Applications	245
<i>C. Costrini, A. Bettidi, M. Calori, A. Cetronio, M. Feudale, C. Lanzieri, C. Proietti</i>	
Advanced Neural Network Techniques for GaN-HEMT Dynamic Behavior Characterization	249
<i>G. Orenco, Paolo Colantonio, Franco Giannini, M. Pirola, V. Camarchia, S. Donati Guerrieri</i>	
A Frequency Domain Extraction Procedure of Low-Pass Equivalent Behavioural Models of Microwave PAs	253
<i>Claudio Siviero, Pedro Miguel Lavrador, Jose Carlos Pedro</i>	
A Distributed Approach for Millimetre-Wave Electron Device Modelling.....	257
<i>D. Resca, A. Santarelli, A. Raffo, R. Cignani, G. Vannini, F. Filicori, A. Cidronali</i>	
Systematic Evaluation of Non-Linear Microwave Device and Amplifier Models.....	261
<i>Dominique Schreurs</i>	
RF-Power Amplifier Modeling and Predistortion Based on a Modular Approach.....	265
<i>P.L. Gilabert, Daniel D. Silveira, G. Montoro, Gottfried Magerl</i>	
A Novel 5-30GHz Voltage Controlled Variable Attenuator with High Linearity in a Low Cost SMD Compact Package.....	269
<i>N. Poitrenaud, B. Lefebvre, S. Tranchant, M. Camiade</i>	
A Novel High Purity, Highly Efficient, Broadband MMIC Frequency Multiplier Implemented in Metamorphic HEMT Technology	273
<i>Andreas Adahl, Herbert Zirath</i>	
An Ultra Compact C-Band 5-Bit MMIC Phase Shifter Based on All-Pass Network.....	277
<i>Kenichi Miyaguchi, Morishige Hieda, Masatake Hangai, Tamotsu Nishino, Norihiro Yunoue, Yoshinobu Sasaki, Moriyasu Miyazaki</i>	
An 8x8 Switch Matrix MMIC Integrating Eight InP-HEMT SP8T Switches for 10-Gbit/s Systems	281
<i>Hideki Kamitsuna, Yasuro Yamane, Masami Tokumitsu, Hirohiko Sugahara, Takatomo Enoki</i>	

Table of Contents

A Physics-Based Nonlinear Model of Microwave P-I-N Diode for CAD	285
<i>Emmanuel Gatard, Philippe Bouysse, Raphael Sommet, Raymond Quere, Jean-Marc Bureau, Pascal Ledieu, Michel Stanislawiak, Clement Tolant</i>	
New Drain Current Model for MESFET/HEMT Devices Based on Pulsed Measurements	289
<i>Guillermo Rafael-Valdivia, Ronan Brady, Thomas J. Brazil</i>	
A Large-Signal Model of GaN HEMTs for Linear High Power Amplifier Design	292
<i>Endalkachew S. Mengistu, Gunter Kompa</i>	
An Electrothermal Model for GaInP/GaAs Power HBTs with Enhanced Convergence Capabilities	296
<i>O. Jardel, Raymond Quere, S. Heckmann, H. Bousbia, Denis Barataud, E. Chartier, D. Floriot</i>	
DC/RF and Statistic Modeling of Four Terminal InGap/GaAs BiFET for Wireless Application	300
<i>C.J. Wei, A. Metzger, Y. Zhu, C. Cismaru, A. Klimashov, P. Zampardi, R. Ramanrata, Y.A. Tkachenko</i>	
Monte Carlo Comparison Between InP-Based Double-Gate and Standard HEMTs	304
<i>B.G. Vasallo, N. Wichmann, S. Bollaert, A. Cappy, T. Gonzalez, D. Pardo, J. Mateos</i>	
Performance Assessment of Nanoscale Multiple Gate MOSFETs (MuGFETs) for RF Applications.....	308
<i>Tao Chuan Lim, Abhinav Kranti, G. Alastair Armstrong</i>	
RF and Noise Performance of Multiple-Gate SOI MOSFETs.....	312
<i>A. Lazaro, B. Iniguez</i>	
Analytical Solution in Complicated Volumes for Detailed Compact Thermal Model Construction.....	316
<i>W. Batty</i>	
Dispersion of Linearity in Broadband FET Circuits	320
<i>Anthony E. Parker, James G. Rathmell</i>	
Frequency Generation for Mobile RFID Reader	324
<i>Sang-Yoon Jeon, Hee-Mun Bang, Sung-Jae Jung, Dong-Hyun Lee, Heung-Bae Lee</i>	
A W-Band MMIC One-Chip Set for Automotive Radar Sensor by Using a 0.15(μ)m mHEMT Process	328
<i>Dong Min Kang, Ju Yeon Hong, Jae Yeob Shim, Hyung Sup Yoon, Kyung Ho Lee</i>	
A Ka-Band MMIC Oscillator Using a Miniaturized CPW 1-D PBG Structure	332
<i>Sang-Gyu Park, Jeong-Hoon Kim, Myeung-Su Kim, Sung-Won Kim, Kwang-Seok Seo, Won-Bae Kim, Jong-In Song</i>	
A Zero-IF Sub-Harmonic Mixer with High LO-RF Isolation Using 0.18 (μ)m CMOS Technology	336
<i>Heng-Ming Hsu, Tai-Hsing Lee</i>	
Microwave Power FET DC Model Extraction Through Isothermal Non-Pulsed Measurements	340
<i>German Torregrosa-Penalva, Alberto Asensio-Lopez, Alvaro Blanco-del-Campo, Jorge Fernandez-Gonzalez</i>	
Low-Temperature DC and RF Measurement and Modelling of InGaAs-InAlAs Resonant Tunneling Diodes Down to 15 K	344
<i>A. Matiss, W. Brockerhoff, A. Poloczek, W. Prost, F.-J. Tegude</i>	
A Fully Integrated 5-6 GHz CMOS Variable-Gain LNA Using Helix-Stacked Inductors.....	348
<i>Chieh-Min Lo, Shih-Fong Chao, Chia-Chi Chang, Huei Wang</i>	
A New Harmonic Noise Frequency Filtering VCO and Mixer Co-Design	352
<i>Jae-Ho Yoon, Nam-Young Kim</i>	
Mixed-Mode Modeling and Parameter Extraction of Advanced InGaAs HBTs in RFIC Systems.....	356
<i>Hsien-Cheng Tseng</i>	
Studies of InGaAs Layers Growth by Metalorganic Chemical Vapor Deposition for InP-HEMTs; Effects of Trimethylindium and Triethylindium	360
<i>Ryuta Sakai, Masahiro Uchida, Gako Araki</i>	

Table of Contents

Study of Field Plate AlGaIn/GaN HEMTs by Means of a 2D-Hydrodynamic Model for Power Applications.....	363
<i>B. Benbakhti, M. Rousseau, J.C. De Jaeger</i>	
Charge Effects and Transient Simulation of p-HEMT Meander Gate Switches	367
<i>M.A. Holm, N.I. Cameron, D.M. Brookbanks</i>	
Wideband and High Gain Cascode Amplifier Using Metamorphic HEMT for Millimeter-Wave Applications.....	371
<i>Sung-Chan Kim, Dan An, Bok-Hyung Lee, Mun-Kyo Lee, Dong-Hoon Shin, Jin-Koo Rhee</i>	
High Performance 94 GHz Resistive Mixer Using GaAs Metamorphic HEMT Technology	375
<i>Dan An, Bok-Hyung Lee, Byeong-Ok Lim, Mun-Kyo Lee, Sung-Chan Kim, Hyun-Chang Park, Jin-Koo Rhee</i>	
A Single-Chip 5GHz WLAN Transmitter in 0.35(μ)m Si/SiGe BiCMOS Technology.....	379
<i>F. Alimenti, M. Borgarino, R. Codeuppi, V. Palazzari, M. Pifferi, L. Roselli, A. Scorzoni, F. Fantini</i>	
Compact Electro-Thermal Modelling and Simulation of InP HBT Based on the Local Reference Concept	383
<i>J. Ding, D. Linton, Derek Smith, Michael B. Steer</i>	
A Non-Quasi-Static, Relaxation-Time Small-Signal HEMT Model Compatible with Large-Signal Modeling	387
<i>Wolfram C. Stiebler</i>	
A Novel Power Plane Topology for Suppressing Parallel-Plate-Resonance Modes in High Speed Printed Circuit Boards.....	391
<i>Seung-Seok Oh, Jung-Min Kim, Jong-Gwan Yook</i>	
Low-Voltage, Low-Power and High-Gain Mixer Based on Unbalanced Mixer Cell	395
<i>No Gil Myoung, Ho Suk Kang, Seok Tae Kim, Byoung Gun Choi, Seong-Su Park, Chul Soon Park</i>	
Three Port Stability Analysis of Broadband Millimetre Wave MMIC Amplifier	399
<i>Beatriz Aja, Eduardo Artal, M. Luisa de la Fuente, Juan Pablo Pascual, Juan Luis Cano</i>	
Implant Isolation Characteristics for SoC Application	403
<i>Sungil Kim, Chulwook Lee, Yongsoon Baek, Jongtae Moon</i>	
Beam Forming Network GaAs Modules for Radioastronomy Focal Plane Arrays	406
<i>W. Ciccognani, F. Di Paolo, Franco Giannini, Ernesto Limiti, P.E. Longhi, A. Serino</i>	
Frequency-Domain Physics-Based Analysis of Semiconductor Devices by a Spectral-Balance Approach	410
<i>Giorgio Leuzzi, Vincenzo Stornelli</i>	
Improved Modified Materka Model for Simulation of Pinch-Off Variation in PHEMT Devices.....	414
<i>Paul M. White, Wolfram C. Stiebler, Philip C. Balas</i>	
A 4.5--5.8 GHz Differential LC VCO Using 0.35 (μ)m SiGe BiCMOS Technology	417
<i>Onur Esame, Ibrahim Tekin, Yasar Gurbuz</i>	
Broadband Active and Passive Balun Circuits: Functional Blocks for Modern Millimeter-Wave Radio Architectures	421
<i>Alberto Costantini, Ben Lawrence, S.J. Mahon, J.T. Harvey, M.G. McCulloch, A. Bessemoulin</i>	
40nm Inprotect LY1.extunderscore 0.7GaAs HEMTs with Novel HSQ Based T-Gate Process.....	425
<i>Sung-Won Kim, Gyung-Seon Seol, Jin-Cherl Her, Kyung-Chul Jang, Kwang-Seok Seo</i>	
GaAs Power pHEMT Characterization for Extracting Nonlinear Parameters of Drain Current by Harmonic Measurement.....	429
<i>Kuan-Yu Chen, Chien-Chang Huang</i>	
A Multi Channel Down-Converter Module Exploiting Recent Advances in Multi Layer RF Packaging Techniques.....	433
<i>S. Rumer, M. Thornber</i>	

Table of Contents

Analysis of Microwave Resonances in a Wirebond Transition Between Conductor-Backed Coplanar Waveguides (CBCPWs).....	437
<i>JuHwan Lim, SungWoo Hwang</i>	
Frequency Domain-Based Approach for Nonlinear Quasi-Static FET Model Extraction from Large-Signal Waveform Measurements	441
<i>T.M. Martin-Guerrero, J.D. Banos-Polglase, C. Camacho-Penalosa, M. Fernandez-Barciela, D.G. Morgan, Paul J. Tasker</i>	
Detailed Analysis of IMD of HBT PA Based on VBIC Model	445
<i>Janne P. Aikio, Joel Vuolevi, Timo Rahkonen</i>	
Integrated Left-Handed Metamaterials on MMIC Technology	449
<i>Hong S. Chua, Philip D. Curtis, Wei Tong, Zhirun Hu, A.A.P. Gibson, Mohamed Missous</i>	
A 3-10GHz Broadband CMOS T/R Switch for UWB Applications	452
<i>K.-H. Pao, C.-Y. Hsu, H.-R. Chuang, C.-L. Lu, C.-Y. Chen</i>	
Foturan Cap and BCB Sealing-Ring for RF MEMS Packaging Applications	456
<i>David Peyrou, Patrick Pons, Arnaud Nicolas, Jun-Wu Tao, Hugues Granier, Robert Plana</i>	
New De-Embedding Technique Based on Cold-FET Measurement	460
<i>G. Pailloncy, Jean-Pierre Raskin</i>	
Four-Port Deembedding Technique for FET Devices Mounted in Hybrid Test Fixture	464
<i>M.A. Yarleque Medina, Dominique Schreurs, Bart Nauwelaers</i>	
LF Noise Analysis of InP/GaAsSb/InP and InP/InGaAs/InP HBTs.....	468
<i>C. Maneux, B. Grandchamp, N. Labat, A. Touboul, M. Riet, J. Godin, Ph. Bove</i>	
Influence of Interconnect Parasitics on the Lateral Scaling of SiGe Power HBTs	472
<i>Guogong Wang, Hao-Chih Yuan, Zhenqiang Ma</i>	
Ultra-Wideband Shielded Vertical via Transitions from DC up to the V-Band	476
<i>T. Kangasvieri, J. Halme, J. Vahakangas, Markku Lahti</i>	
30-Watt Power Amplifier for 3.5GHz WiMAX Base Station Application.....	480
<i>M. Sarfraz, M. Akkul</i>	
44-GHz High Power and Driver Microstrip Amplifier MMICs Using 6-Inch 0.15-(μ)m PHEMTs	483
<i>A. Dadello, A. Fattorini, S.J. Mahon, A. Bessemoulin, J.T. Harvey</i>	
GaN HEMT Performance --- Measurements and Simulations of a 3.6 mm Device from Cree	487
<i>Asher Madjar, Zygmund Turski, Yifei Li</i>	
Advances in GaN-Based Discrete Power Devices for L- and X-Band Applications.....	490
<i>Joachim Wurfl, Reza Behtash, Richard Lossy, Armin Liero, Wolfgang Heinrich, Gunther Trankle, Klaus Hirche, G. Fischer</i>	
Microwave Class-F and Inverse Class-F Power Amplifiers Designs Using GaN Technology and GaAs pHEMT.....	493
<i>S. Gao, P. Butterworth, A. Sambell, C. Sanabria, H. Xu, S. Heikman, U. Mishra, R.A. York</i>	
RF-MEMS Technology Platform for Agile Mobile and Satellite Communications.....	497
<i>X. Rottenberg, P. Soussan, S. Stoukatch, P. Czarnecki, Bart Nauwelaers, G. Carchon, I. De Wolf, W. De Raedt, H.A.C. Tilmans</i>	
Broadband RF-MEMS Based SPDT.....	501
<i>Sergio DiNardo, Paola Farinelli, Flavio Giacomozzi, Giovanni Mannocchi, Romolo Marcelli, Benno Margesin, Paolo Mezzanotte, Viviana Mulloni, Peter Russer, Roberto Sorrentino, Francesco Vitulli, Larissa Vietzorreck</i>	
In-Plane Electrostatically-Actuated RF MEMS Switch Suspended on a Low-Resistivity Substrate.....	505
<i>David Girbau, Lluís Pradell, A. Lazaro, Alvar Nebot</i>	

Table of Contents

Simplified RF-MEMS Switches Using Implanted Conductors and Thermal Oxide.....	509
<i>Christian Siegel, Volker Ziegler, Bernhard Schonlinner, Ulrich Prechtel, Hermann Schumacher</i>	
Contactless Dielectric Charging Mechanisms in RF-MEMS Capacitive Switches	513
<i>G.J. Papaioannou, G. Wang, D. Bessas, John Papapolymerou</i>	
Compact K-Band Watt-Level GaAs PHEMT Power Amplifier MMIC with Integrated ESD Protection	517
<i>A. Bessemoulin, M.G. McCulloch, A. Alexander, D. McCann, S.J. Mahon, J.T. Harvey</i>	
Constant Linearity Variable Gain Traveling Wave Amplifier MMIC for 1 to 26.5 GHz Applications	521
<i>Kohei Fujii, Henrik Morkner</i>	
On-Chip Active Gate Bias Circuit for MMIC Amplifier Applications with 100% Threshold Voltage Variation Compensation	525
<i>A.P. de Hek, E.B. Busking</i>	
A Millimeter-Wave Highly Linear VCO MMIC with Compact Tuning Voltage Converter	529
<i>Hiroyuki Mizutani, Masaomi Tsuru, Takayuki Matsuzuka, Kenichiro Choumei, Kenji Kawakami, Moriyasu Miyazaki</i>	
A High Performance 20--42 GHz MMIC Frequency Multiplier with Low Input Drive Power and High Output Power	533
<i>Sushil Kumar, Henrik Morkner</i>	
Low-Loss Microstrip Surface-Mount K-Band Package.....	537
<i>Kamran Entesari, Gabriel M. Rebeiz</i>	
PCS Power Amplifier Module Package Using Selectively Anodized Aluminum Substrate	541
<i>Seong-Ho Shin, Ju-Hyang Lee, Bo-In Sohn, Seung-Han Ryu, Young-Se Kwon</i>	
Advanced 3D Packaging Using Novel Liquid Crystalline Polymer Based Substrates.....	545
<i>Camil-Daniel Ghiu, Sidharth Dalmia, Jack Vickers, Larry Carastro, Winston Czakon, Venky Sundaram, George White</i>	
Thermal Characterisation of LTCC Frontend Modules with Integrated Power Amplifiers for Wireless LAN Application	548
<i>Kostyantyn Markov, Torsten Keiler, Alexander Chernyakov, Ciaran Curtin, Patric Heide</i>	
A Rigorous Comparison of Package and PCB Effects on Micromixer- and Gilbert Mixer-Based Upconverter MMICs	552
<i>F.Y. Han, J.M. Wu, T.S. Horng</i>	